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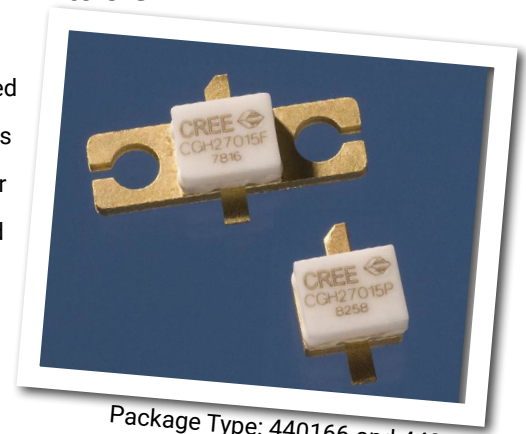
Address: A1208, Overseas Decoration Building, #122 Zhenhua RD., Futian, Shenzhen, China



CGH27015

15 W, 28V, GaN HEMT for Linear Communications ranging from VHF to 3 GHz

Cree's CGH27015 is a gallium nitride (GaN) high electron mobility transistor designed specifically for high efficiency, high gain and wide bandwidth capabilities, which makes the CGH27015 ideal for VHF, Comms, 3G, 4G, LTE, 2.3-2.9GHz WiMAX and BWA amplifier applications. The unmatched transistor is available in both screw-down, flange and solder-down, pill packages.



Package Type: 440166 and 440196
PN: CGH27015F and CGH27015P

Typical Performance 2.3-2.7 GHz ($T_c = 25^\circ\text{C}$)

Parameter	2.3 GHz	2.4 GHz	2.5 GHz	2.6 GHz	2.7 GHz	Units
Small Signal Gain	16.9	16.0	15.1	14.6	14.3	dB
EVM at $P_{AVE} = 33$ dBm	1.69	1.51	1.50	1.66	1.93	%
Drain Efficiency at $P_{AVE} = 33$ dBm	27.1	27.8	28.4	28.0	28.0	dB

Note:

Measured in the CGH27015F-AMP amplifier circuit, under 802.16 OFDM, 3.5 MHz Channel BW, 1/4 Cyclic Prefix, 64 QAM Modulated Burst, 5 ms Burst, Symbol Length of 59, Coding Type RS-CC, Coding Rate Type 2/3, PAR = 9.8 dB @ 0.01 % Probability on CCDF.

Features



- VHF - 3.0 GHz Operation
- 15 W Peak Power Capability
- 14.5 dB Small Signal Gain
- 2 W $P_{AVE} < 2.0$ % EVM
- 28 % Efficiency at 2 W Average Power
- Designed for WiMAX Fixed Access 802.16-2004 OFDM Applications
- Designed for WiMAX Mobile Access 802.16e OFDMA Applications

Large Signal Models Available for ADS and MWO

Absolute Maximum Ratings (not simultaneous) at 25°C Case Temperature

Parameter	Symbol	Rating	Units	Units
Drain-Source Voltage	V_{DS}	84	Volts	25°C
Gate-to-Source Voltage	V_{GS}	-10, +2	Volts	25°C
Storage Temperature	T_{STG}	-65, +150	°C	
Operating Junction Temperature	T_J	225	°C	
Maximum Forward Gate Current	I_{GMAX}	4.0	mA	25°C
Maximum Drain Current ¹	I_{DMAX}	1.5	A	25°C
Soldering Temperature ²	T_S	245	°C	
Screw Torque	τ	60	in-oz	
Thermal Resistance, Junction to Case ³	$R_{\theta JC}$	8.0	°C/W	85°C
Case Operating Temperature ³	T_C	-40, +150	°C	

Note:

¹ Current limit for long term, reliable operation.

² Refer to the Application Note on soldering at www.cree.com/RF/Document-Library

³ Measured for the CGH27015F at $P_{DISS} = 14W$.

Electrical Characteristics ($T_C = 25^\circ C$)

Characteristics	Symbol	Min.	Typ.	Max.	Units	Conditions
DC Characteristics¹						
Gate Threshold Voltage	$V_{GS(th)}$	-3.8	-3.0	-2.3	V_{DC}	$V_{DS} = 10 V, I_D = 3.6 mA$
Gate Quiescent Voltage	$V_{GS(Q)}$	-	-2.7	-	V_{DC}	$V_{DS} = 28 V, I_D = 100 mA$
Saturated Drain Current	I_{DS}	2.9	3.5	-	A	$V_{DS} = 6.0 V, V_{GS} = 2.0 V$
Drain-Source Breakdown Voltage	V_{BR}	120	-	-	V_{DC}	$V_{GS} = -8 V, I_D = 3.6 mA$
RF Characteristics^{2,3} ($T_C = 25^\circ C, F_0 = 2.5 GHz$ unless otherwise noted)						
Small Signal Gain	G_{SS}	13	15	-	dB	$V_{DD} = 28 V, I_{DQ} = 100 mA$
Drain Efficiency ⁴	η	20	28	-	%	$V_{DD} = 28 V, I_{DQ} = 100 mA, P_{AVE} = 33 dBm$
Error Vector Magnitude	EVM	-	2.0	-	%	$V_{DD} = 28 V, I_{DQ} = 100 mA, P_{AVE} = 33 dBm$
Output Mismatch Stress	VSWR	-	-	10 : 1	Ψ	No damage at all phase angles, $V_{DD} = 28 V, I_{DQ} = 100 mA, P_{AVE} = 33 dBm$ OFDM P_{AVE}
Dynamic Characteristics						
Input Capacitance	C_{GS}	-	4.5	-	pF	$V_{DS} = 28 V, V_{gs} = -8 V, f = 1 MHz$
Output Capacitance	C_{DS}	-	1.3	-	pF	$V_{DS} = 28 V, V_{gs} = -8 V, f = 1 MHz$
Feedback Capacitance	C_{GD}	-	0.2	-	pF	$V_{DS} = 28 V, V_{gs} = -8 V, f = 1 MHz$

Notes:

¹ Measured on wafer prior to packaging.

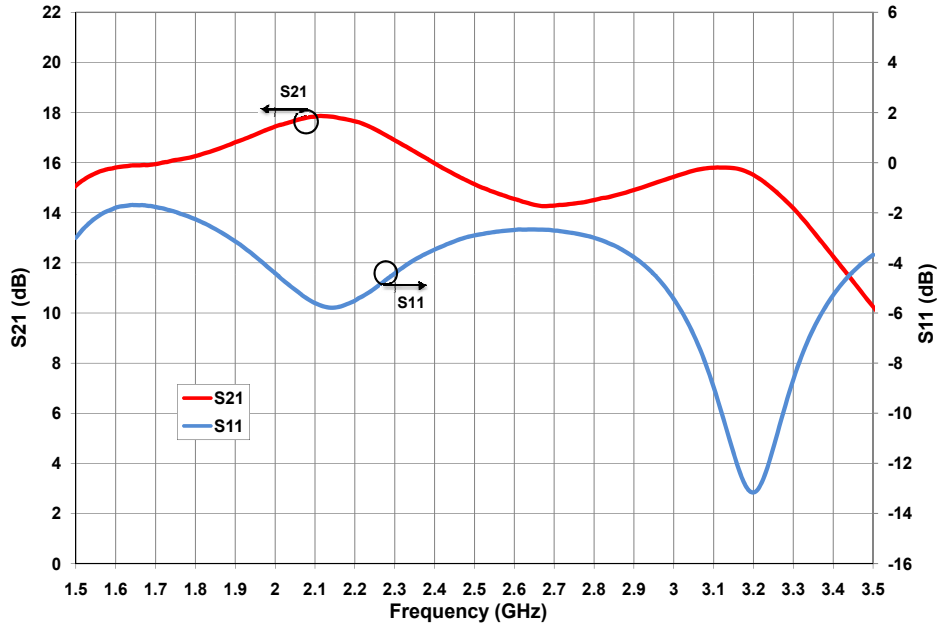
² Measured in the CGH27015F-AMP test fixture.

³ Under 802.16 OFDM, 3.5 MHz Channel BW, 1/4 Cyclic Prefix, 64 QAM Modulated Burst, 5 ms Burst, Symbol Length of 59, Coding Type RS-CC, Coding Rate Type 2/3, PAR = 9.8 dB @ 0.01 % Probability on CCDF.

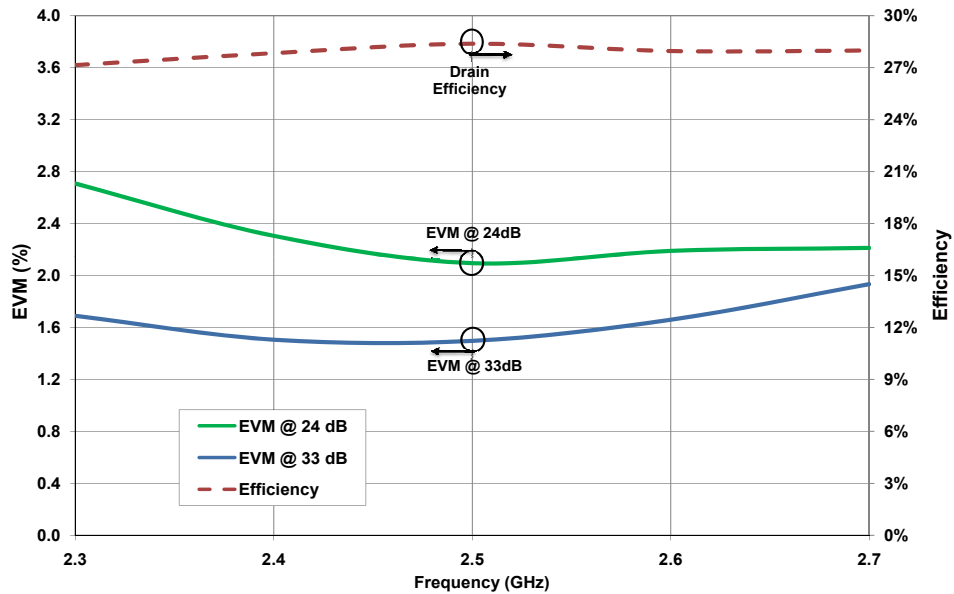
⁴ Drain Efficiency = P_{OUT} / P_{DC} .

Typical Performance Data

Performance of CGH27015 in Broadband Amplifier Circuit
 $V_{DD} = 28\text{ V}$, $I_{DQ} = 100\text{ mA}$



Typical EVM and Efficiency at 24dB and 33 dB vs Frequency of CGH27015 in Broadband Amplifier Circuit

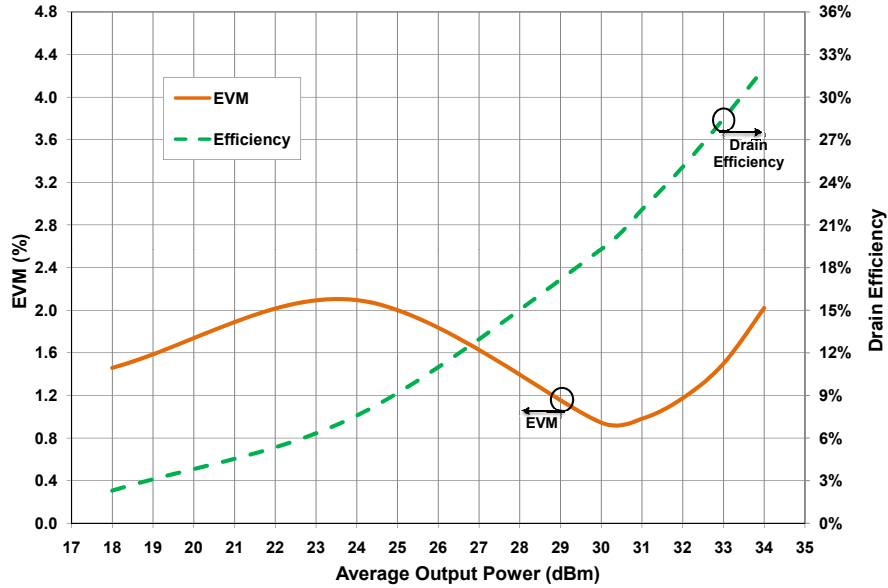


Note:

Under 802.16 OFDM, 3.5 MHz Channel BW, 1/4 Cyclic Prefix, 64 QAM Modulated Burst, Symbol Length of 59, Coding Type RS-CC, Coding Rate Type 2/3.

Typical Performance Data

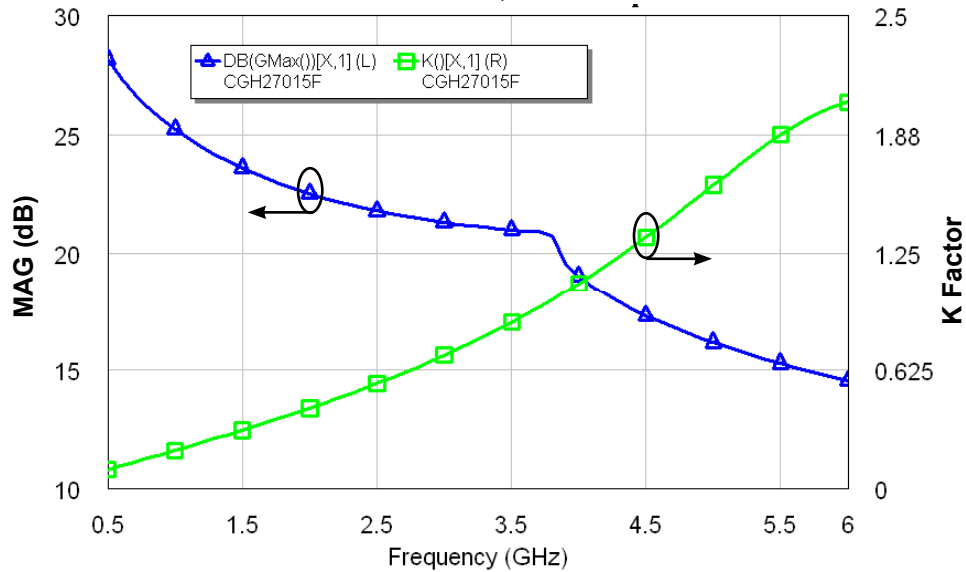
Typical EVM and Efficiency of CGH27015 in Broadband Amplifier Circuit at 2.5 GHz
F=2.5 GHz, 802.16-2004 OFDM, P/A=9.8 dB



Note:

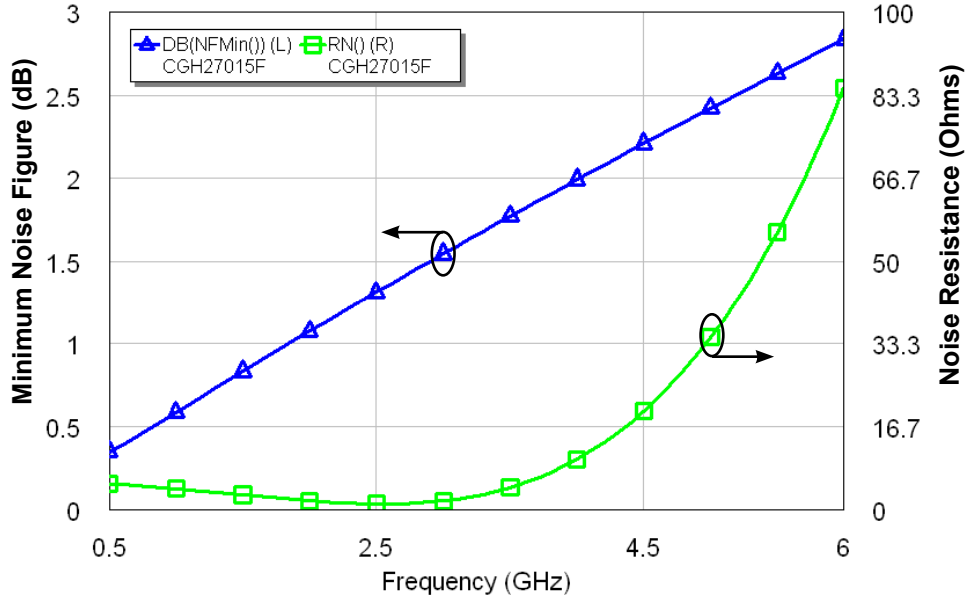
Under 802.16-2004 OFDM, 3.5 MHz Channel BW, 1/4 Cyclic Prefix, 64 QAM Modulated Burst, Symbol Length of 59, Coding Type RS-CC, Coding Rate Type 2/3.

Simulated Maximum Available Gain and K Factor of the CGH27015F
V_{DD} = 28 V, I_{DQ} = 100 mA



Typical Noise Performance

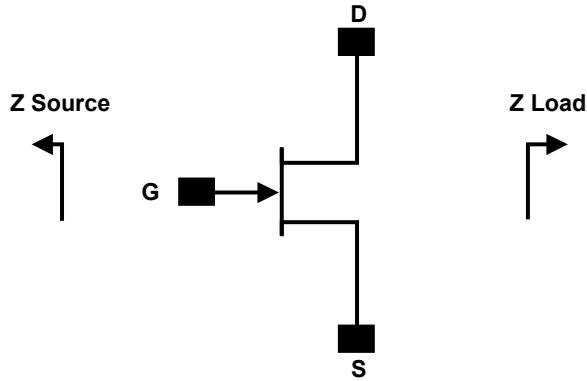
Simulated Minimum Noise Figure and Noise Resistance vs Frequency of the CGH27015
 $V_{DD} = 28\text{ V}$, $I_{DQ} = 100\text{ mA}$



Electrostatic Discharge (ESD) Classifications

Parameter	Symbol	Class	Test Methodology
Human Body Model	HBM	1A (> 250 V)	JEDEC JESD22 A114-D
Charge Device Model	CDM	II (200 < 500 V)	JEDEC JESD22 C101-C

Source and Load Impedances

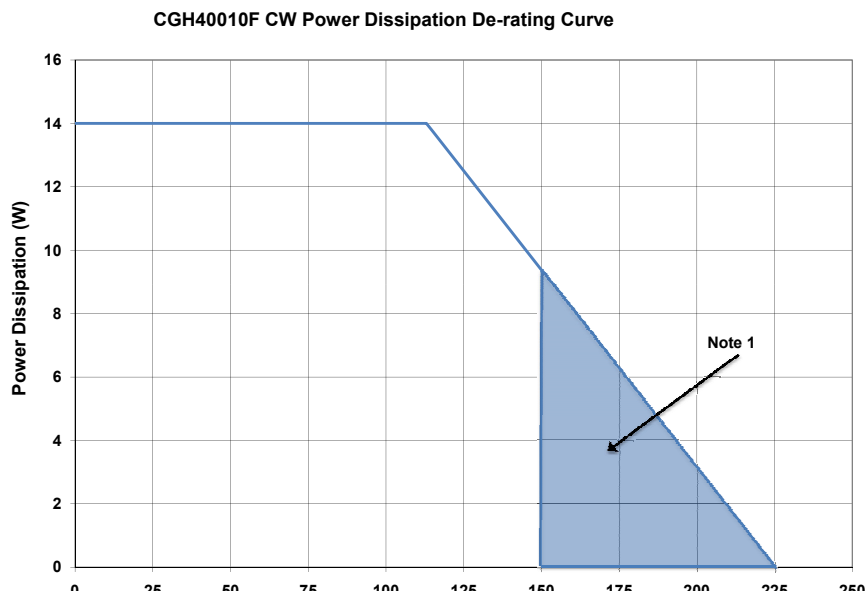


Frequency (MHz)	Z Source	Z Load
2300	17.8 - j1.5	16.8 - j1.7
2400	20.3 - j4.0	16.9 - j0.8
2500	20.6 - j7.9	17.2 + j0.2
2600	18.2 - j11.3	17.7 + j1.3
2700	14.6 - j12.6	19.1 + j2.4

Note 1. $V_{DD} = 28V$, $I_{DQ} = 200mA$ in the 440166 package.

Note 2. Impedances are extracted from the CGH27015-AMP demonstration amplifier and are not source and load pull data derived from the transistor.

CGH27015 Power Dissipation De-rating Curve

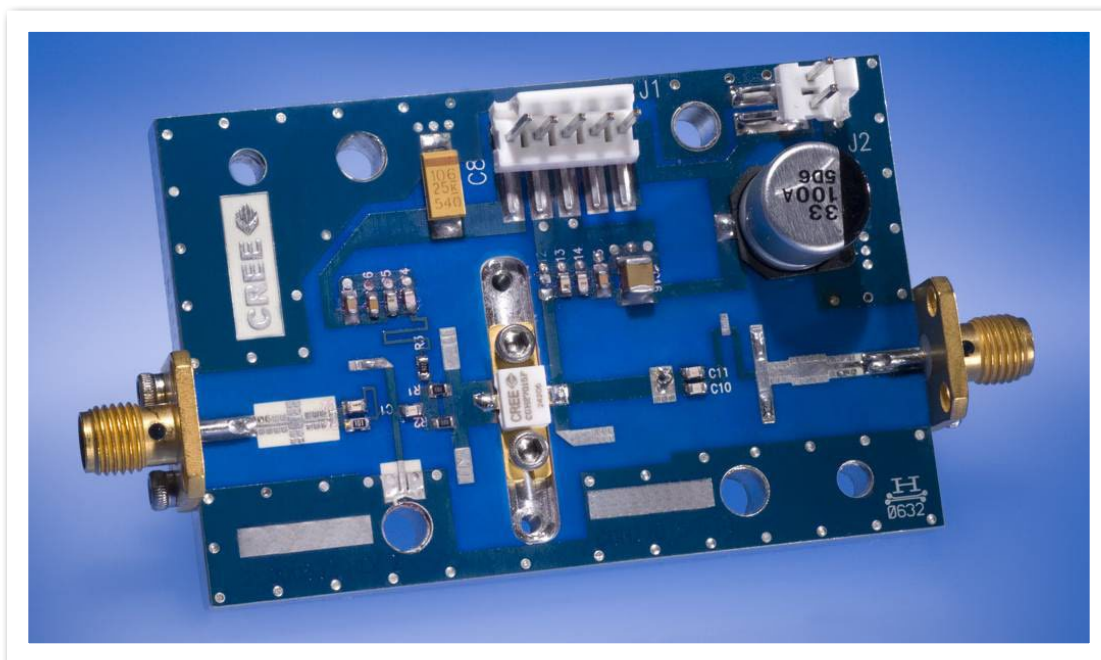


Note 1. Area exceeds Maximum Case Operating Temperature (See Page 2).

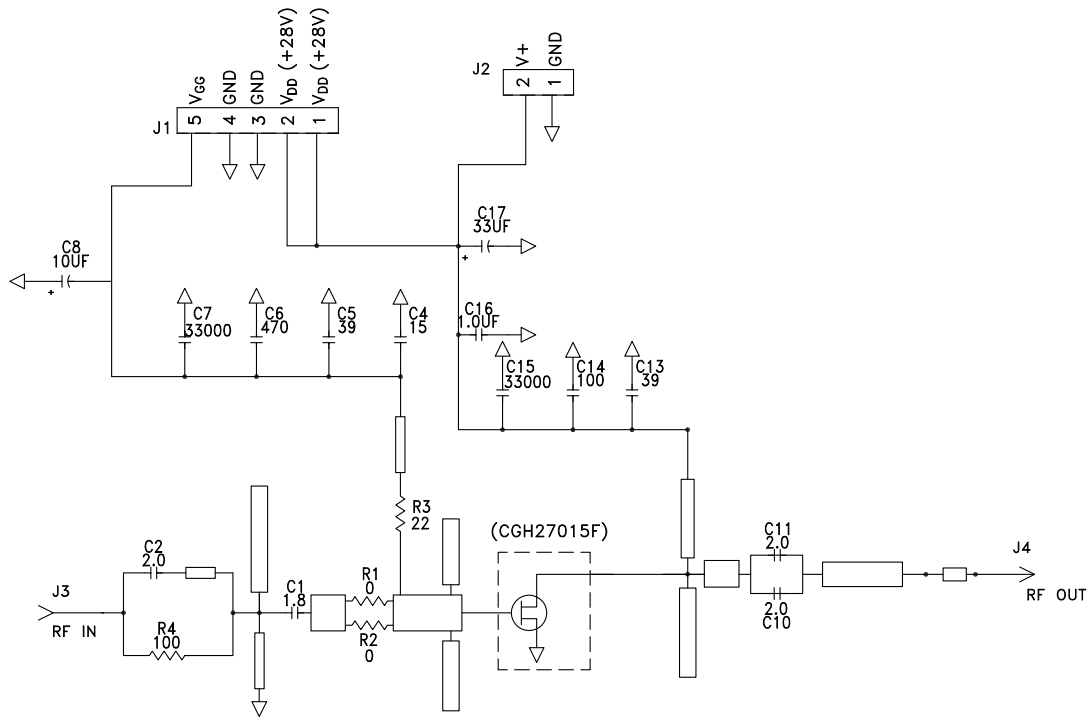
CGH27015-AMP Demonstration Amplifier Circuit Bill of Materials

Designator	Description	Qty
R1,R2	RES,1/16W,0603,1%,0 OHMS	2
R4	RES,1/16W,0603,1%,100 OHMS	1
R3	RES,1/16W,0603,1%,22.6 OHMS	1
C6	CAP, 470PF, 5%,100V, 0603	1
C17	CAP, 33 UF, 20%, G CASE	1
C16	CAP, 1.0UF, 100V, 10%, X7R, 1210	1
C8	CAP 10UF 16V TANTALUM	1
C14	CAP, 100.0pF, +/-5%, 0603	1
C4	CAP, 15pF, +/-5%, 0603	1
C1	CAP, 1.8pF, +/-0.1pF, 0603	1
C2, C10, C11	CAP, 2.0pF, +/-0.1pF, 0603	3
C5,C13	CAP, 39pF, +/-5%, 0603	2
C7,C15	CAP,33000PF, 0805,100V, X7R	2
J3,J4	CONN SMA STR PANEL JACK RECP	1
J2	HEADER RT>PLZ.1CEN LK 2 POS	1
J1	HEADER RT>PLZ. .1CEN LK 5POS	1
-	PCB, R04350B, Er = 3.48, h = 20 mil	1
-	CGH27015F or CGH27015P	1

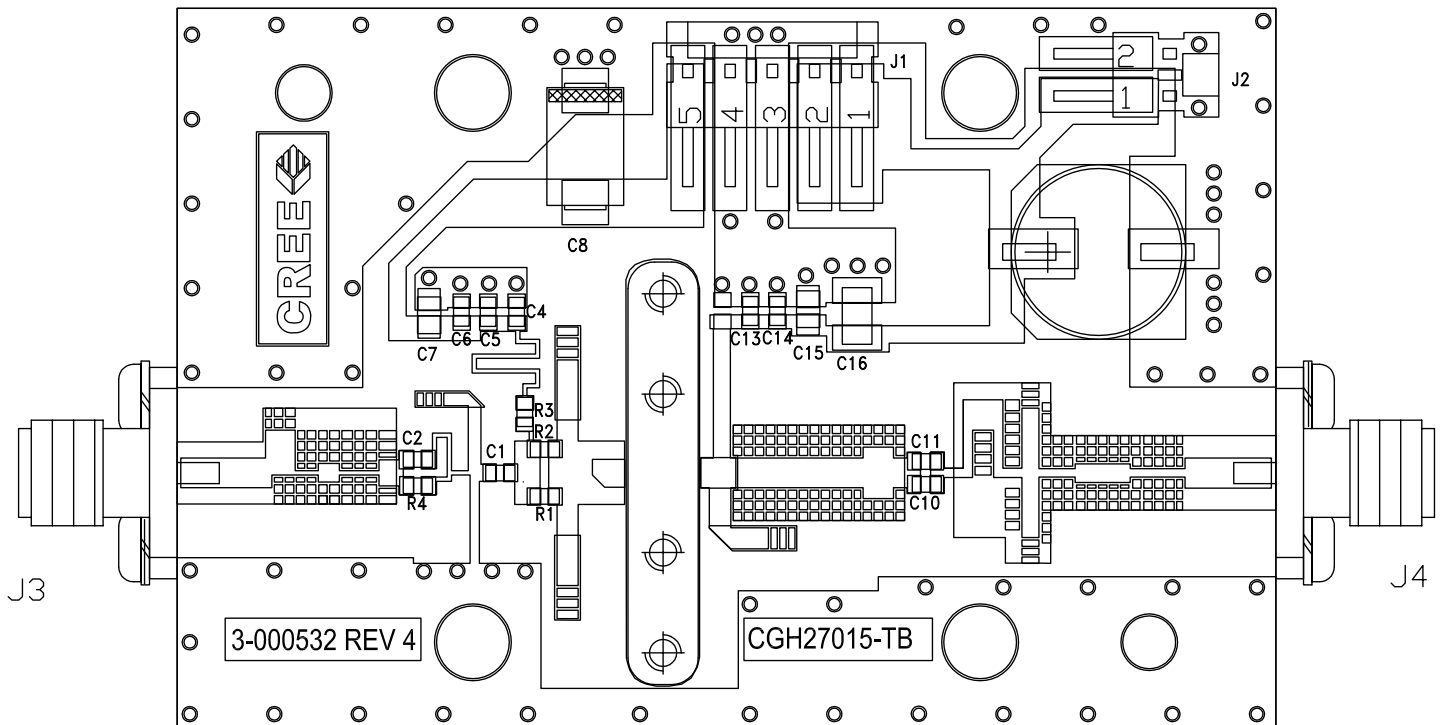
CGH27015-AMP Demonstration Amplifier Circuit



CGH27015-AMP Demonstration Amplifier Circuit Schematic



CGH27015-AMP Demonstration Amplifier Circuit Outline

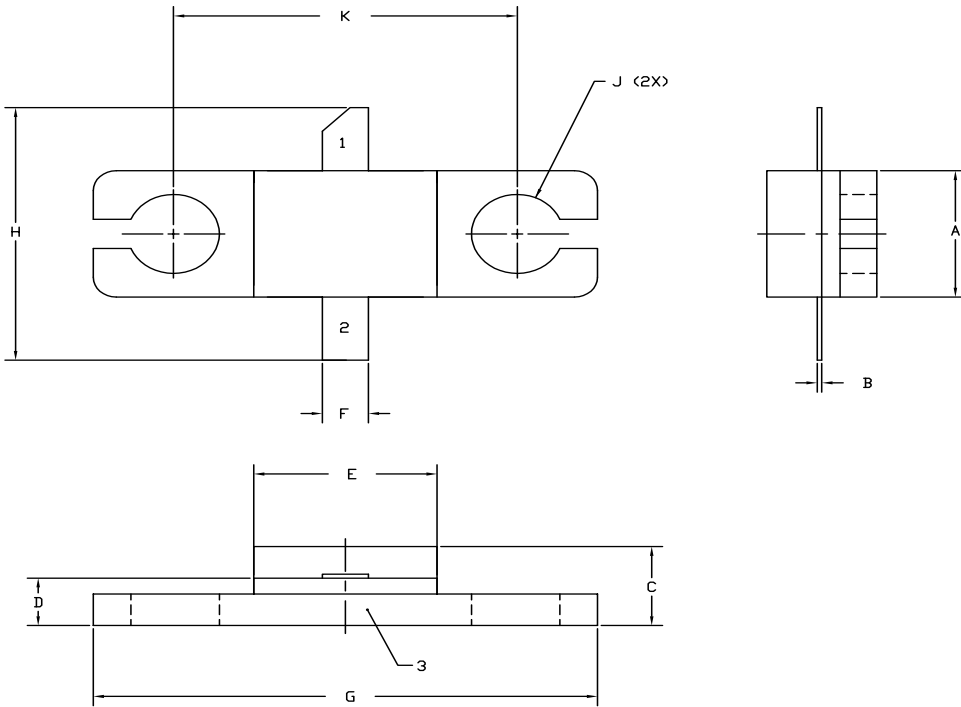


Typical Package S-Parameters for CGH27015
 (Small Signal, $V_{DS} = 28\text{ V}$, $I_{DQ} = 100\text{ mA}$, angle in degrees)

Frequency	Mag S11	Ang S11	Mag S21	Ang S21	Mag S12	Ang S12	Mag S22	Ang S22
500 MHz	0.909	-124.41	17.41	107.81	0.026	21.06	0.335	-93.73
600 MHz	0.902	-134.04	15.04	101.48	0.027	15.39	0.322	-101.61
700 MHz	0.898	-141.62	13.18	96.16	0.028	10.74	0.315	-107.78
800 MHz	0.894	-147.78	11.71	91.54	0.028	6.79	0.312	-112.73
900 MHz	0.892	-152.91	10.51	87.43	0.028	3.35	0.312	-116.77
1.0 GHz	0.890	-157.30	9.53	83.68	0.028	0.28	0.314	-120.15
1.1 GHz	0.889	-161.12	8.71	80.20	0.028	-2.51	0.318	-123.04
1.2 GHz	0.889	-164.51	8.01	76.95	0.028	-5.07	0.322	-125.57
1.3 GHz	0.888	-167.56	7.41	73.86	0.028	-7.45	0.328	-127.82
1.4 GHz	0.888	-170.34	6.89	70.91	0.028	-9.69	0.335	-129.87
1.5 GHz	0.888	-172.91	6.44	68.07	0.028	-11.81	0.342	-131.77
1.6 GHz	0.888	-175.30	6.04	65.32	0.028	-13.82	0.349	-133.56
1.7 GHz	0.888	-177.55	5.69	62.65	0.027	-15.74	0.357	-135.25
1.8 GHz	0.888	-179.68	5.37	60.05	0.027	-17.58	0.364	-136.89
1.9 GHz	0.888	178.29	5.09	57.50	0.027	-19.34	0.373	-138.48
2.0 GHz	0.888	176.34	4.83	55.01	0.027	-21.04	0.381	-140.03
2.1 GHz	0.889	174.45	4.60	52.56	0.026	-22.69	0.389	-141.55
2.2 GHz	0.889	172.63	4.39	50.14	0.026	-24.27	0.397	-143.06
2.3 GHz	0.889	170.84	4.20	47.76	0.026	-25.80	0.405	-144.56
2.4 GHz	0.889	169.10	4.02	45.41	0.025	-27.28	0.413	-146.04
2.5 GHz	0.890	167.39	3.86	43.09	0.025	-28.70	0.421	-147.52
2.6 GHz	0.890	165.71	3.71	40.79	0.025	-30.08	0.429	-149.00
2.7 GHz	0.891	164.04	3.57	38.51	0.024	-31.41	0.437	-150.48
2.8 GHz	0.891	162.39	3.44	36.26	0.024	-32.69	0.445	-151.95
2.9 GHz	0.891	160.76	3.32	34.01	0.024	-33.92	0.452	-153.43
3.0 GHz	0.892	159.13	3.21	31.79	0.023	-35.10	0.459	-154.92
3.2 GHz	0.892	155.89	3.00	27.38	0.023	-37.31	0.473	-157.90
3.4 GHz	0.893	152.65	2.83	23.00	0.022	-39.32	0.486	-160.90
3.6 GHz	0.893	149.39	2.67	18.66	0.021	-41.09	0.499	-163.93
3.8 GHz	0.894	146.09	2.54	14.34	0.020	-42.63	0.510	-166.99
4.0 GHz	0.894	142.74	2.41	10.02	0.020	-43.90	0.521	-170.10
4.2 GHz	0.895	139.33	2.31	5.70	0.019	-44.88	0.530	-173.24
4.4 GHz	0.895	135.84	2.21	1.37	0.018	-45.53	0.539	-176.45
4.6 GHz	0.895	132.26	2.12	-2.98	0.018	-45.84	0.547	-179.71
4.8 GHz	0.895	128.59	2.04	-7.36	0.017	-45.78	0.554	176.97
5.0 GHz	0.895	124.80	1.97	-11.79	0.016	-45.32	0.561	173.56
5.2 GHz	0.895	120.90	1.91	-16.27	0.016	-44.47	0.566	170.07
5.4 GHz	0.895	116.87	1.85	-20.81	0.016	-43.25	0.571	166.48
5.6 GHz	0.895	112.70	1.80	-25.41	0.015	-41.72	0.575	162.78
5.8 GHz	0.895	108.38	1.75	-30.10	0.015	-39.97	0.579	158.96
6.0 GHz	0.895	103.92	1.70	-34.88	0.016	-38.13	0.581	155.00

To download the s-parameters in s2p format, go to the [CGH27015 Product Page](#) and click on the documentation tab.

Product Dimensions CGH27015F (Package Type – 440166)



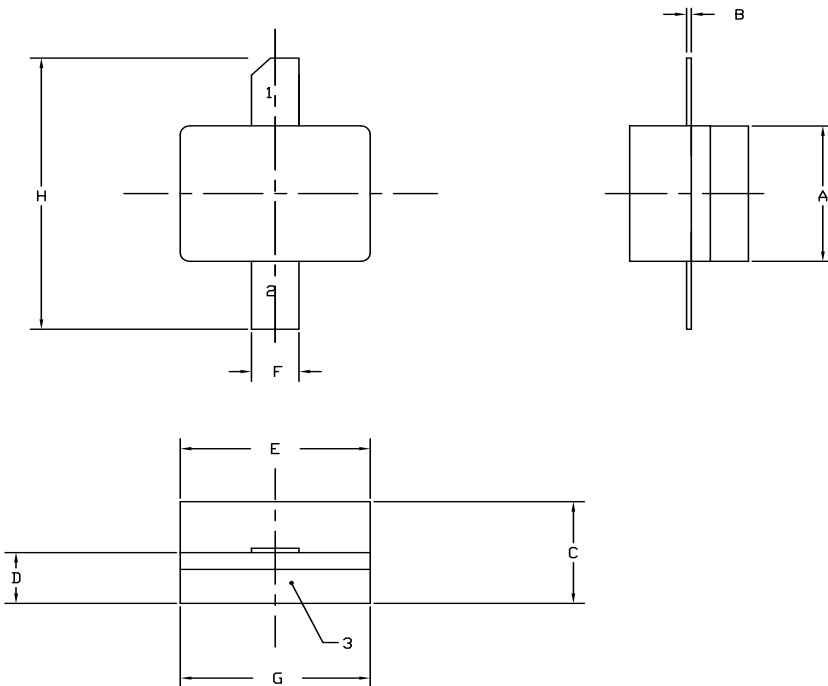
NOTES:

1. DIMENSIONING AND TOLERANCING PER ANSI Y14.5M, 1982.
2. CONTROLLING DIMENSION: INCH.
3. ADHESIVE FROM LID MAY EXTEND A MAXIMUM OF 0.020" BEYOND EDGE OF LID.
4. LID MAY BE MISALIGNED TO THE BODY OF THE PACKAGE BY A MAXIMUM OF 0.008" IN ANY DIRECTION.
5. ALL PLATED SURFACES ARE NI/AU

DIM	INCHES		MILLIMETERS	
	MIN	MAX	MIN	MAX
A	0.155	0.165	3.94	4.19
B	0.004	0.006	0.10	0.15
C	0.115	0.135	2.92	3.43
D	0.057	0.067	1.45	1.70
E	0.195	0.205	4.95	5.21
F	0.045	0.055	1.14	1.40
G	0.545	0.555	13.84	14.09
H	0.280	0.360	7.11	9.14
J	∅ .100		2.54	
K	0.375		9.53	

- PIN 1. GATE
 PIN 2. DRAIN
 PIN 3. SOURCE

Product Dimensions CGH27015P (Package Type – 440196)



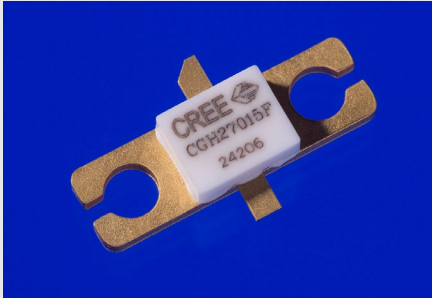

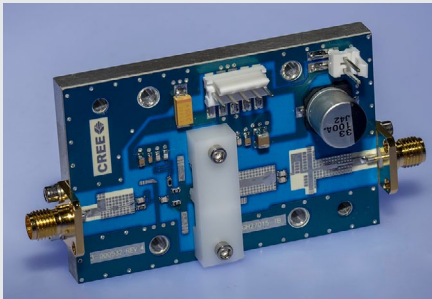
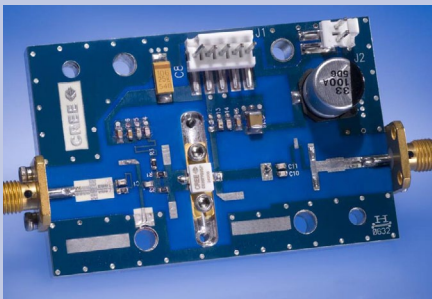
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DIM	INCHES		MILLIMETERS	
	MIN	MAX	MIN	MAX
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B	0.003	0.006	0.10	0.15
C	0.115	0.135	2.92	3.17
D	0.057	0.067	1.45	1.70
E	0.195	0.205	4.95	5.21
F	0.045	0.055	1.14	1.40
G	0.195	0.205	4.95	5.21
H	0.280	0.360	7.11	9.14

- PIN 1. GATE
 PIN 2. DRAIN
 PIN 3. SOURCE

Product Ordering Information

Order Number	Description	Unit of Measure	Image
CGH27015F	GaN HEMT	Each	
CGH27015P	GaN HEMT	Each	
CGH27015F-TB	Test board without GaN HEMT	Each	
CGH27015F-AMP	Test board with GaN HEMT installed	Each	



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